

## ABSTRACT

A semiconductor treating device [[(1)]] includes treating chamber [[(2)]] connected to a common transportation chamber [[(8)]] and treating a substrate [[(W)]] to be treated. A gas supply system [[(40)]] for supplying system [[(40)]] for supplying a predetermined gas to each of the treating chambers [[(2)]] is attached to each chamber. The gas supply system [[(40)]] has a primary side connection unit [[(23)]] connected to the source of the predetermined gas and has a flow rate control unit [[(2)]] . The primary side connection unit [[(23)]] connected to the source of the predetermined gas and has a flow rate control unit [[(2)]] . The primary side connection unit [[(23)]] is placed on the lower side of the corresponding treating chamber [[(2)]] . The flow rate control unit [[(2)]] is placed on a gas line for supplying the gas from the primary side connection unit [[(23)]] to the corresponding treating chamber [[(2)]] . The flow rate control unit [[(2)]] is provided such that at least a part of it is superposed on the upper side of the primary side connection unit [[(23)]] .